

Isc N-Channel MOSFET Transistor

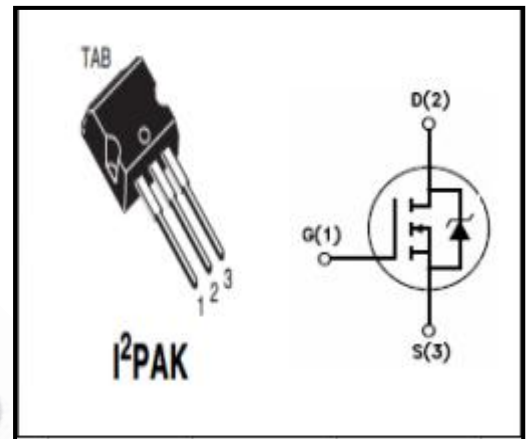
STB11NM60FD-1

• FEATURES

- With To-262(I²PAK) package
- Low input capacitance and gate charge
- Low gate input resistance
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

• APPLICATIONS

- Switching applications



• ABSOLUTE MAXIMUM RATINGS(T_a=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V _{DSS}	Drain-Source Voltage	600	V
V _{GSS}	Gate-Source Voltage	±30	V
I _D	Drain Current-Continuous@T _c =25°C T _c =100°C	11 7	A
I _{DM}	Drain Current-Single Pulsed	44	A
P _D	Total Dissipation	160	W
T _j	Operating Junction Temperature	-65~150	°C
T _{stg}	Storage Temperature	-65~150	°C

• THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R _{th(ch-c)}	Channel-to-case thermal resistance	0.78	°C/W
R _{th(ch-a)}	Channel-to-ambient thermal resistance	62.5	°C/W

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ELECTRICAL CHARACTERISTICS

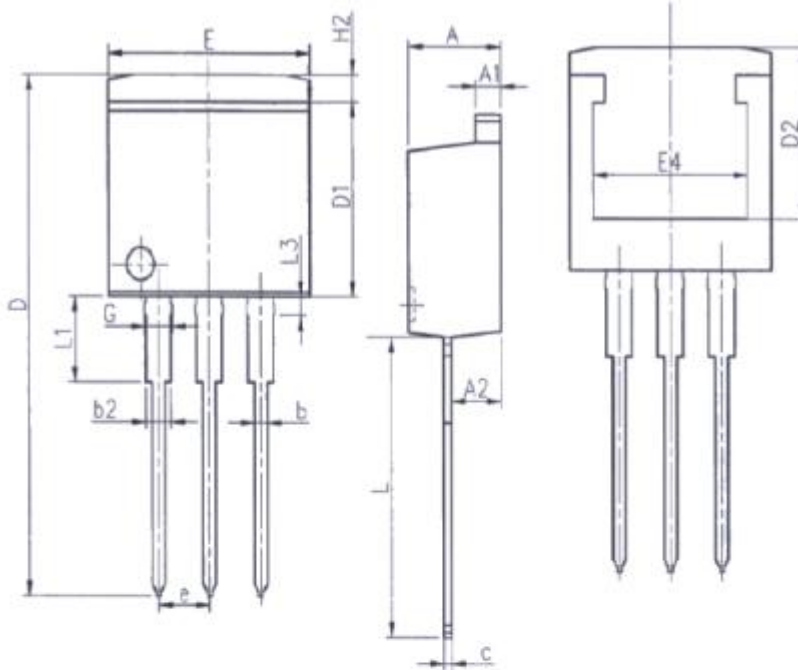
T_C=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V; I _D = 0.25mA	600			V
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =±30V; I _D =0.25mA	3		5	V
R _{DS(on)}	Drain-Source On-Resistance	V _{GS} = 10V; I _D =5.5A		400	450	mΩ
I _{GSS}	Gate-Source Leakage Current	V _{GS} = ±30V; V _{DS} = 0V			±0.1	μA
I _{DSS}	Drain-Source Leakage Current	V _{DS} = 600V; V _{GS} = 0V; T _J =25°C T _J =125°C			1 100	μA
V _{SDF}	Diode forward voltage	I _{SD} =11A, V _{GS} = 0 V			1.5	V

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STI24NM60N

DIMENSIONAL DRAWING



Unit: mm		
Symbol	Min.	Max.
A	4.37	4.77
A1	1.22	1.42
A2	2.47	2.87
b	0.70	0.97
b2	1.17	1.42
c	0.28	0.53
D	23.20	24.02
D1	8.38	8.90
D2	6.00	-

Unit: mm		
Symbol	Min.	Max.
E	9.90	10.39
E4	7.30	-
e	2.54BSC	
G	1.25	1.50
H2	-	1.31
L	13.34	14.10
L1	3.30	4.06
L3	0.95	1.15